7

7



(b)

(a)

(b)

Q-4

Seat No.: Enrolment No. **GUJARAT TECHNOLOGICAL UNIVERSITY** BE - SEMESTER-VIII(OLD) EXAMINATION - WINTER 2017 Date: 02-11-2017 Subject Code: 180802 **Subject Name: VLSI Technologies** Time: 02:30 pm TO 5:00 pm **Total Marks: 70 Instructions:** 1. Attempt all questions. 2. Make suitable assumptions wherever necessary. 3. Figures to the right indicate full marks. Explain the VLSI design flow by Y-chart and its simplified view Q-1 (a) Discuss basic steps of fabrication. 7 **(b)** 7 **Explain Channel Length Modulation** \mathbf{O} -2 (a) **(b)** Explain energy band diagram of MOS structure at surface inversion and derive the 7 equation of threshold voltage. OR Derive the expression for drain current as a function of VGS, VDS and VSB for all 7 Q-2**(b)** three region of operation of MOSFET using Gradual Channel Approximation. Explain the functioning of depletion load nMOS inverter and derive critical voltage 7 Q-3 (a) points VOH, VOL, VIL and VIH. Give the delay time definitions and calculation of delay times. 7 **(b)** OR Draw two types of enhancement – load n-MOS inverter circuits and compare both. 7 Q-3 (a) 7 Write a short note on MOSFET Capacitance. **(b)** Concept of regularity, modularity and locality. **Q-4** (a) 7

7 Ad HOC testable design techniques **Q-5** (a) Explain the basic principle of pass transistor circuit. Explain logic "1" transfer and 7 logic "0" transfer.

OR

Explain the criteria to measure the design quality to improve the chip design and 7 **Q-5** (a) explain any two in brief. 7

Write a short note on Built In Self Test (BIST). **(b)**

Explain Device Isolation Technique and Locos.

Explain CMOS Transmission gates (or Pass Gates).

Write a short note on FPGA.